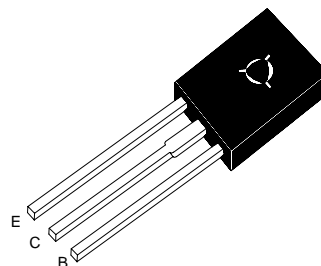


ST 2SD882H

NPN Silicon Power Transistor

The transistor is subdivided into four groups, R, Q, P and E, according to its DC-DC current gain.

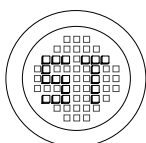


TO-18 Plastic Package

Absolute Maximum Ratings

	Symbol	Value	Unit
Collector to Base Voltage	V_{CBO}	60	V
Collector to Emitter Voltage	V_{CEO}	30	V
Emitter to Base Voltage	V_{EBO}	5	V
Collector Current (D.C)	$I_C(\text{DC})$	3	A
Collector Current (pulse)	$I_C(\text{pulse})$	7	A
Total power dissipation($T_a=25^\circ\text{C}$)	P_{tot}	1	W
Total power dissipation($T_c=25^\circ\text{C}$)	P_{tot}	10	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_s	-55 to +150	$^\circ\text{C}$

G S P FORM A IS AVAILABLE



®

РАДИОТЕХ-ТРЕЙД

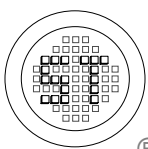
Тел.: (495) 795-0805
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Эл. почта: info@rct.ru
Веб: www.rct.ru

ST 2SD882H

Characteristics at $T_{amb}=25\text{ }^{\circ}\text{C}$

	Symbol	Min.	Typ.	Max.	Unit	
DC Current Gain at $V_{CE}=2\text{V}$, $I_C=1\text{A}$ Current Gain Group	R	h_{FE}	60	-	120	-
	Q	h_{FE}	100	-	200	-
	P	h_{FE}	160	-	320	-
	E	h_{FE}	200	-	400	-
		h_{FE}	30	150	-	-
at $V_{CE}=2\text{V}$, $I_C=20\text{mA}$						
Collector Cutoff Current at $V_{CB}=60\text{V}$	I_{CBO}	-	-	1.0	μA	
Emitter Cutoff Current at $V_{EB}=3.0\text{V}$	I_{EBO}	-	-	1.0	μA	
Output Capacitance $V_{CB}=10\text{V}$, $f=1.0\text{MHz}$	C_{ob}	-	45	-	pF	
Base Emitter Saturation Voltage at $I_C=2.0\text{mA}$, $I_B=0.2\text{A}$	$V_{BE(sat)}$	-	1.0	2.0	V	
Collector Emitter Saturation Voltage at $I_C=2.0\text{mA}$, $I_B=0.2\text{A}$	$V_{CE(sat)}$	-	0.3	0.5	V	
Gain Bandwidth Product at $V_{CE}=5.0\text{V}$, $I_C=0.1\text{A}$	f_T	-	90	-	MHz	

G S P FORM A IS AVAILABLE



SEMTECH ELECTRONICS LTD.

(Subsidiary of Semtech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)



ISO/TS 16949 : 2002
Certificate No. 05103



ISO 14001
Certificate No. 7116



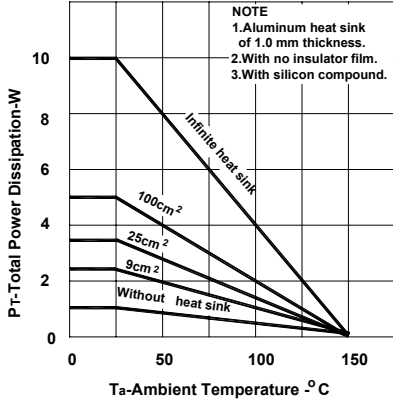
ISO 9001 : 2000
Certificate No. 6509-1999-00-002-001

Dated : 07/12/2002

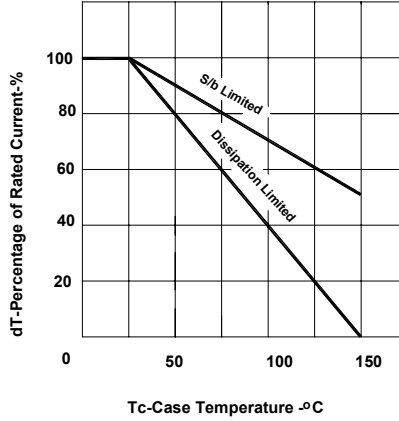
ST 2SD882H

TYPICAL CHARACTERISTICS (Ta=25°C)

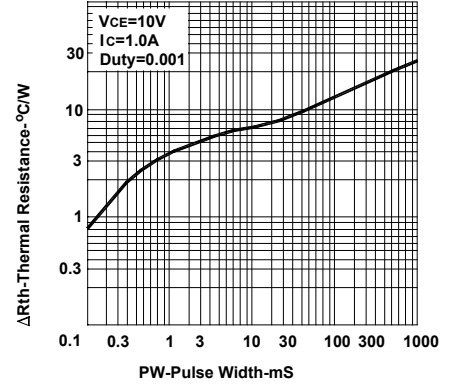
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



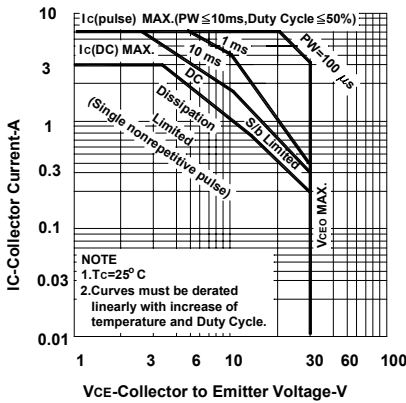
DERATING CURVES FOR ALL TYPES



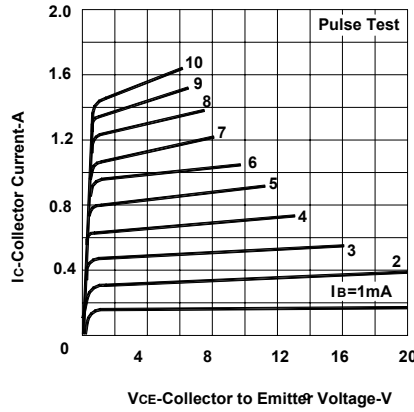
THERMAL RESISTANCE vs. PULSE WIDTH



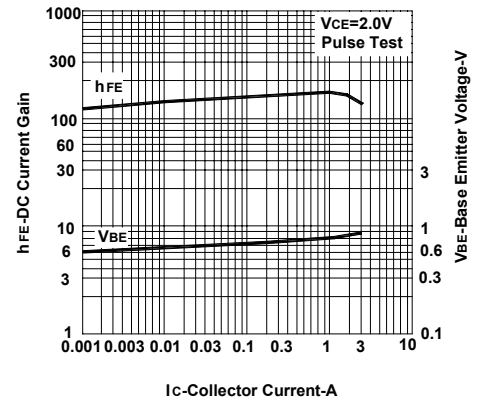
SAFE OPERATING AREAS



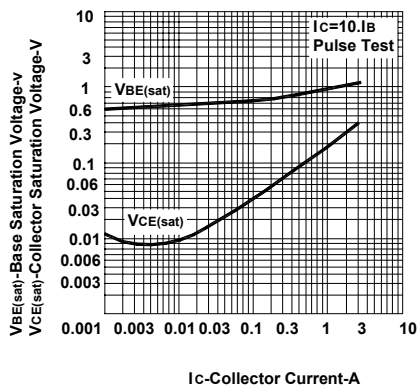
COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



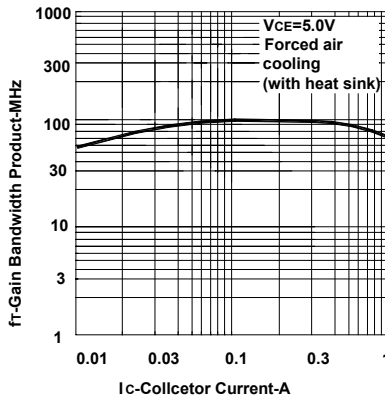
DC CURRENT GAIN, BASE TO EMITTER VOLTAGE vs. COLLECTOR CURRENT



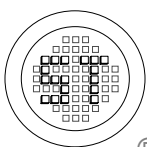
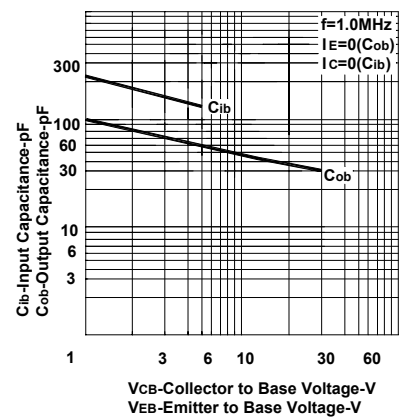
BASE AND COLLECTOR SATURATION VOLTAGE vs. COLLECTOR CURRENT



GAIN BANDWIDTH PRODUCT vs. COLLECTOR CURRENT

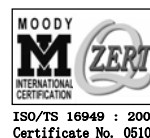


INPUT AND OUTPUT CAPACITANCE vs. REVERSE VOLTAGE



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